

# 144N12N-VB Datasheet

## N-Channel 100-V (D-S) MOSFET

### PRODUCT SUMMARY

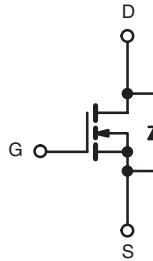
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
100	0.010 at $V_{GS} = 10$ V	100
	0.023 at $V_{GS} = 4.5$ V	85

### FEATURES

- Trench Power MOSFET
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC


**RoHS**  
 COMPLIANT

TO-263



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	100	A
		75 <sup>a</sup>	
Pulsed Drain Current	$I_{DM}$	300	
Avalanche Current	$I_{AS}$	75	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	280	mJ
Maximum Power Dissipation <sup>b</sup>	$P_D$	250 <sup>c</sup>	W
		3.75	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	$R_{thJA}$	40	°C/W
		62.5	
Junction-to-Case	$R_{thJC}$	0.6	

Notes:

- a. Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %.  
 b. Guaranteed by design, not subject to production testing.  
 c. Independent of operating temperature.

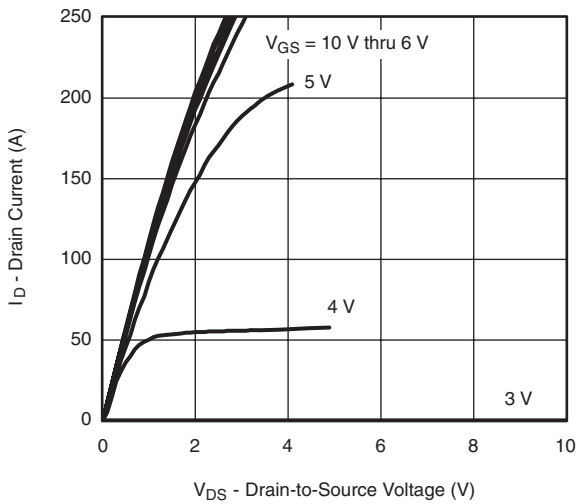
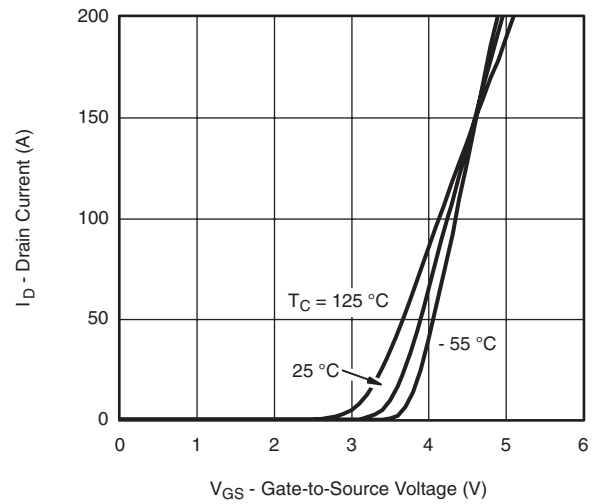
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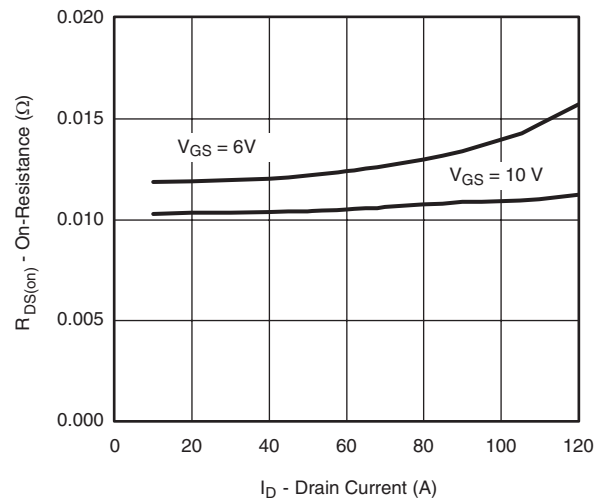
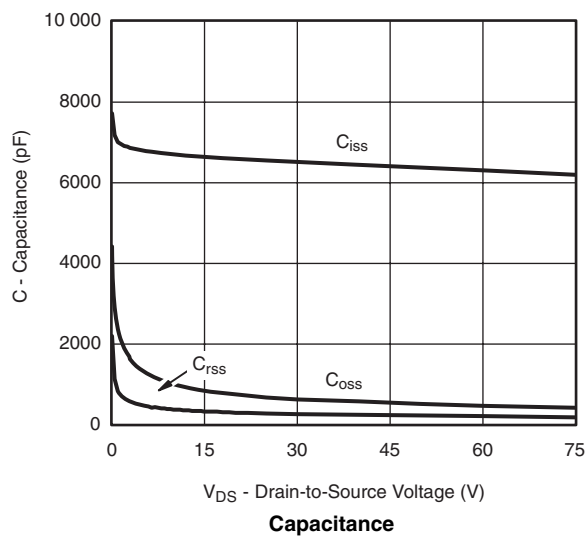
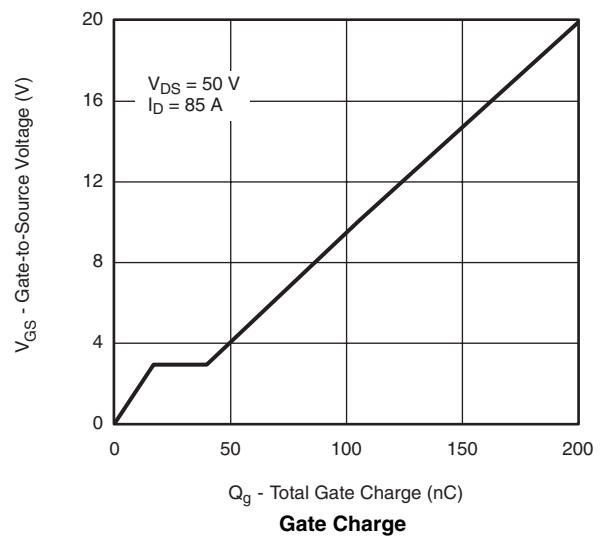
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^{\circ}\text{C}$			50	
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^{\circ}\text{C}$			250	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = \geq 5\text{ V}, V_{GS} = 10\text{ V}$	120			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.010		$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		0.023		
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$		0.020		
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$		0.030		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	25			S
Dynamic <sup>b</sup>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		6550		pF
Output Capacitance	$C_{oss}$			665		
Reverse Transfer Capacitance	$C_{rss}$			265		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 85\text{ A}$		105	160	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			17		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			23		
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 85\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		12	25	ns
Rise Time <sup>c</sup>	$t_r$			90	135	
Turn-Off DelayTime <sup>c</sup>	$t_{d(off)}$			55	85	
Fall Time <sup>c</sup>	$t_f$			130	195	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^{\circ}\text{C}$ <sup>b</sup>						
Continuous Current	$I_S$				85	A
Pulsed Current	$I_{SM}$				240	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 85\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F = 50\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		85	140	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			4.5	7	A
Reverse Recovery Charge	$Q_{rr}$			0.17	0.35	$\mu\text{C}$

Notes:

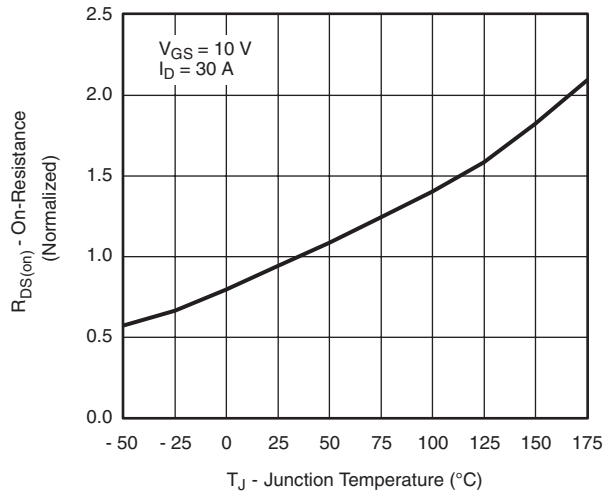
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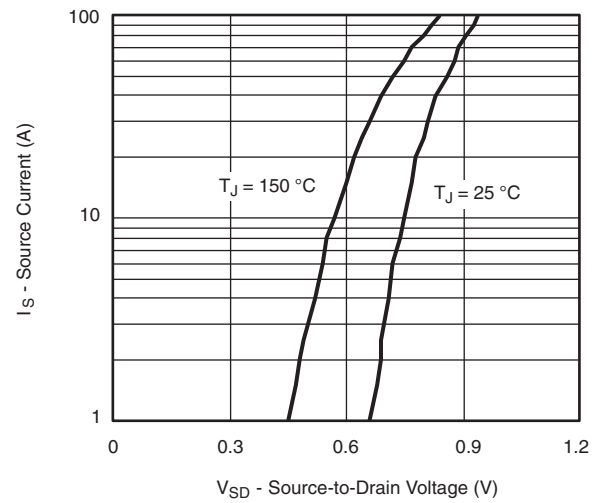
**TYPICAL CHARACTERISTICS**  $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted

**Output Characteristics**

**Transfer Characteristics**

**Transconductance**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

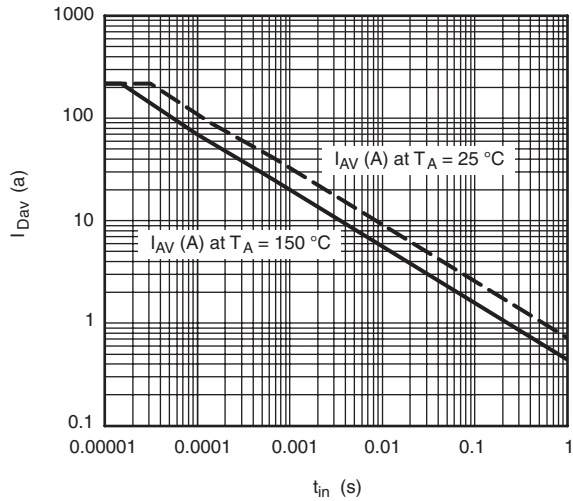
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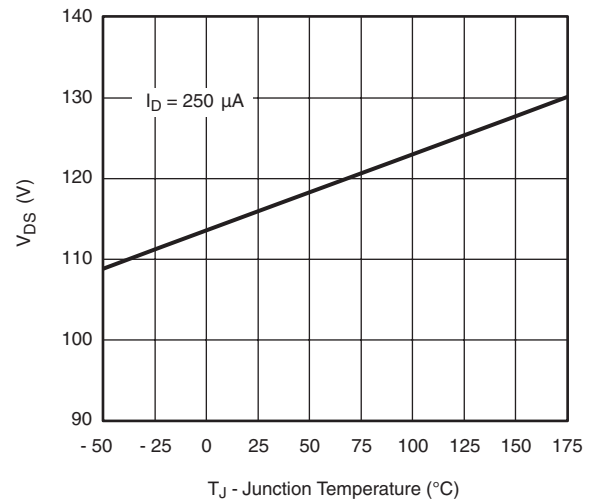
**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**



**Avalanche Current vs. Time**

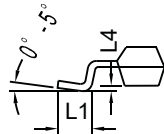
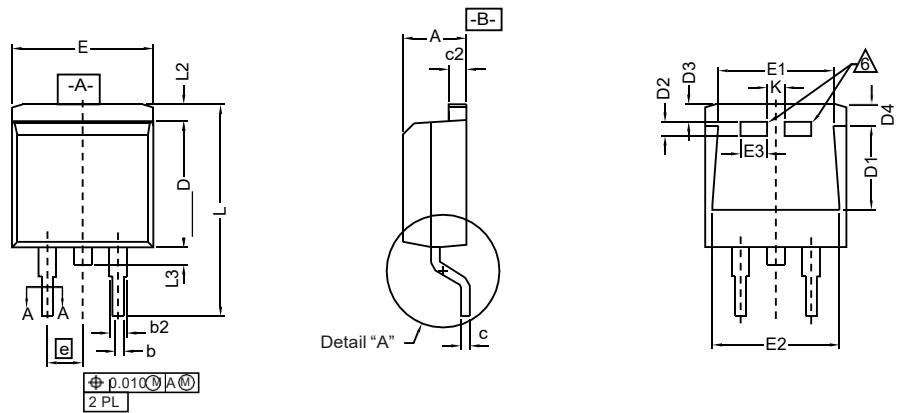


**$T_J$  - Drain-Source Breakdown vs. Junction-Temperature**

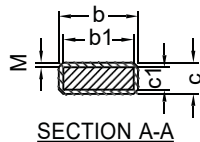
## THERMAL RATINGS



# TO-263 (D<sup>2</sup>PAK): 3-LEAD



DETAIL A (ROTATED 90°)




SECTION A-A

DIM.		INCHES		MILLIMETERS	
		MIN.	MAX.	MIN.	MAX.
A		0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
b1		0.020	0.035	0.508	0.889
b2		0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2		0.045	0.055	1.143	1.397
D		0.340	0.380	8.636	9.652
D1		0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
D3		0.045	0.055	1.143	1.397
D4		0.044	0.052	1.118	1.321
E		0.380	0.410	9.652	10.414
E1		0.245	-	6.223	-
E2		0.355	0.375	9.017	9.525
E3		0.072	0.078	1.829	1.981
e		0.100 BSC		2.54 BSC	
K		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
M		-	0.002	-	0.050
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

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DWG: 5843

## Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- \*: Thin lead is for SUB, SYB.  
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
-  This feature is for thick lead.

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